

## isc Silicon NPN Power Transistor

2SC3156

## DESCRIPTION

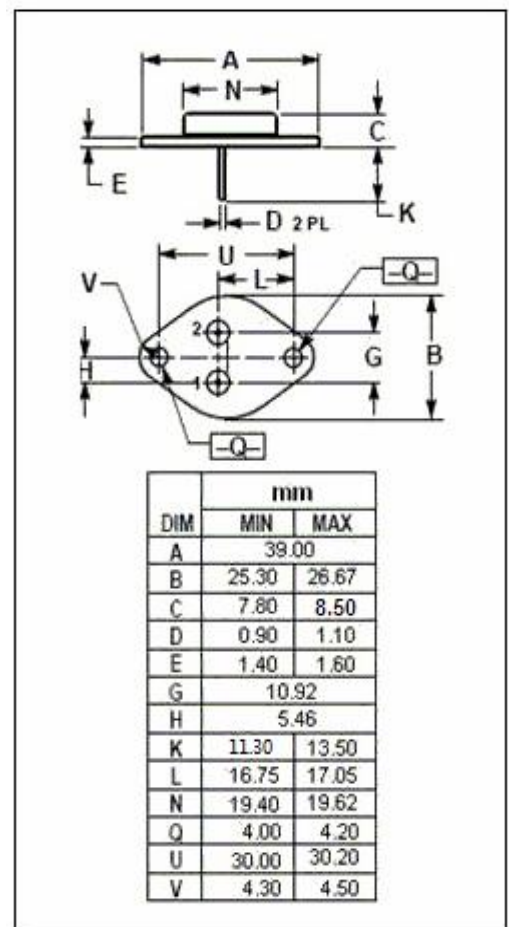
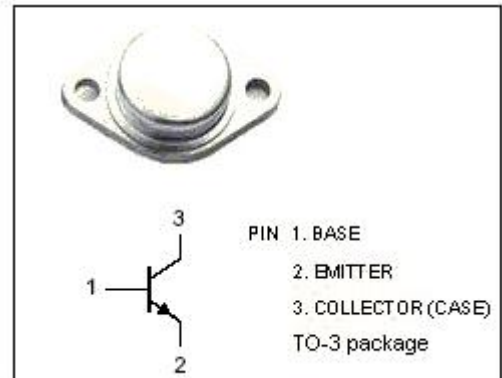
- High Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 800V(\text{Min})$
- Fast Switching Speed
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

- Switching regulator and high voltage switching applications

ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	900	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	6	A
$I_{CM}$	Collector Current-Peak	20	A
$I_B$	Base Current-Continuous	3	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	120	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistor****2SC3156****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}$ ; $R_{BE}=\infty$	800			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}$ ; $I_E=0$	900			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}$ ; $I_C=0$	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}$ ; $I_B=0.6\text{A}$			2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=3\text{A}$ ; $I_B=0.6\text{A}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=800\text{V}$ ; $I_E=0$			10	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}$ ; $I_C=0$			10	$\mu\text{A}$
$h_{FE-1}$	DC Current Gain	$I_C=0.4\text{A}$ ; $V_{CE}=5\text{V}$	10			
$h_{FE-2}$	DC Current Gain	$I_C=2\text{A}$ ; $V_{CE}=5\text{V}$	8			
$f_T$	Current-Gain—Bandwidth Product	$I_C=0.4\text{A}$ ; $V_{CE}=10\text{V}$		15		MHz
$C_{OB}$	Output Capacitance	$I_E=0$ ; $V_{CB}=10\text{V}$		120		pF

## Switching times

$t_r$	Rise Time	$I_C=4\text{A}$ ; $I_{B1}=0.8\text{A}$ ; $I_{B2}=-1.6\text{A}$ ; $R_L=100\Omega$ ; $V_{CC}=400\text{V}$			1.0	$\mu\text{s}$
$t_{stg}$	Storage Time				2.5	$\mu\text{s}$
$t_f$	Fall Time				0.7	$\mu\text{s}$

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